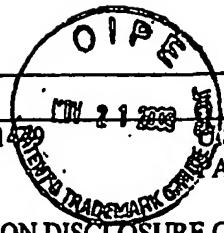


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INFORMATION DISCLOSURE CITATION

Title: MIM Multilayer Capacitor

ATTY. DOCKET NO. 51889/5 US APPLICATION NO. 10/664,666

APPLICANT - Douglas R. Hackler, Sr. et al.

FILING DATE-
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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
8	18	03091974 A	17.04.91	Japan			<input checked="" type="checkbox"/>
	19						
	20						
	21						
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	23						
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OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication, etc.)

W	26	Kim et al., "Development of CVD-Ru/Ta ₂ O ₅ /CVD-Ru Capacitor with Concave Structure for Multigigabit-scale DRAM Generation," 2001 IEEE, pgs. 12.1.1-12.1.4.
CY	27	Aoki et al., "Robust 130nm-Node Cu Dual Damascene Technology with Low-k Barrier SiCN," 2001 IEEE, pgs. 4.2.1-4.2.4.
TV	28	Samavati et al., "Fractal Capacitors," IEEE Journal of Solid-State Circuits, Vol. 33, No. 12, December 1998, pgs. 2035-2041.
CY	29	Kotecki et al., "(Ba, Sr) TiO dielectrics for future stacked-capacitor DRAM," IBM J. Res. Develop., Vol. 42, No. 3, May 1999, pg. 367-382.
S	30	Media for SolidState Technology, "Interfacial reaction and thermal stability of Ta ₂ O ₅ /TiN for metal electrode capacitors," http://solidstate.articles.printhis.clickability.com/pt/cpt?action=cpt&expire=&urlID=8160 , 11/4/2003, pgs. 1-7.
	31	
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